

## Keynote Speaker

**Gaudenzio Meneghesso** (Univ. of Padova), “*Reliability of GaN HEMTs*”

## Invited Speakers (tentative)

- 1) **Tomas Palacios**, MIT, “*GaN Fin FET Technology for Power and RF Applications*”
- 2) **Michael Uren**, University of Bristol, “*Device Instabilities in GaN/AlGaN HEMTs – the Key Role of Leakage*”
- 3) **Primit Parikh**, Transphorm Inc., “*Qualified GaN Transistor Technology for Automotive Applications*” (tentative)
- 4) **Katsunori Ueno**, Fuji Electric, “*MOSFETs on Mg implanted GaN and the application to vertical DIMOSFETs*”
- 5) **Shinya Ohmagari**, AIST, “*Dislocation reduction in diamond by metal-assisted termination (MAT) and their improvements in Schottky barrier diode characteristics*”
- 6) **Takashi Taniguchi**, NIMS, “*Single Crystalline Hexagonal Boron Nitride for Far UV Emission and Substrate for 2D Opto-Electric Devices*”
- 7) **Siddharth Rajan**, Ohio State Univ., “*Materials and Device Engineering for Gallium Oxide Electronics*”
- 8) **Kentaro Kaneko**, Kyoto Univ., “*P-type  $\alpha$ -(Ir,Ga)<sub>2</sub>O<sub>3</sub> thin films in Gallium Oxide Electronics*”
- 9) **Shintaro Shinjo**, Mitsubishi Electric, “*Recent Advancement of GaN HEMT Power Amplifiers for 5G Mobile Wireless System*”
- 10) **Jeong-Sun Moon**, HRL, “*High-speed graded channel GaN HEMTs for linear millimeter-wave applications*”
- 11) **Dae-Hyun Kim**, Kyungpook National Univ., “*Ultra High-Speed InP-based HEMTs for Logic Application, L<sub>g</sub> = 87 nm InAlAs/InGaAs HEMTs with 3S/mm*” (tentative)
- 12) **Masahiro Asada**, Tokyo Tech., “*Recent progress on terahertz sources using resonant tunneling diodes and applications*”

- 13) **Young-Kai Chen**, DARPA, “*Advanced mm-Wave Power Electronics*”
- 14) **Jr-Tai Chen**, SweGaN, “*Progress in buffer-free GaN-on-SiC HEMT heterostructures for microwave and power devices*”
- 15) **Fumimasa Horikiri**, SCIOCS Corp., “*GaN wet etching process*”
- 16) **Elke Meissner**, Fraunhofer IISB, “*Materials defects in power HEMT structures and their consequences on the electrical performance of the devices*”
- 17) **Huili Grace Xing**, Cornell Univ. “*Power Electronics Based on GaN and Ga<sub>2</sub>O<sub>3</sub> Bulk Substrates*”
- 18) **Hiroyuki Handa**, Panasonic Corp., “*Next Generation GaN Power Devices using GaN Substrates*”
- 19) **Takuji Hosoi**, Osaka Univ., “*Gate stack engineering for GaN power MOSFETs*”